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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	24MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	51
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	24K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f100rct6btr

List of figures

1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32F100xC, STM32F100xD and STM32F100xE value line microcontrollers. In the rest of the document, the STM32F100xC, STM32F100xD and STM32F100xE are referred to as high-density value line devices.

This STM32F100xC, STM32F100xD and STM32F100xE datasheet should be read in conjunction with the STM32F100xx high-density ARM®-based 32-bit MCUs *reference manual (RM0059)*. For information on programming, erasing and protection of the internal Flash memory please refer to the *STM32F100xx high-density value line Flash programming manual (PM0072).* The reference and Flash programming manuals are both available from the STMicroelectronics website *www.st.com.*

For information on the Cortex®-M3 core please refer to the Cortex®-M3 Technical Reference Manual, available from the http://infocenter.arm.com.

2.2 Overview

2.2.1 ARM® Cortex®-M3 core with embedded Flash and SRAM

The ARM Cortex®-M3 processor is the latest generation of ARM processors for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced system response to interrupts.

The ARM Cortex®-M3 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices.

The STM32F100xx value line family having an embedded ARM core, is therefore compatible with all ARM tools and software.

2.2.2 Embedded Flash memory

Up to 512 Kbytes of embedded Flash memory is available for storing programs and data.

2.2.3 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

2.2.4 Embedded SRAM

Up to 32 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states.

2.2.5 FSMC (flexible static memory controller)

The FSMC is embedded in the high-density value line family. It has four Chip Select outputs supporting the following modes: SRAM, PSRAM, and NOR.

Functionality overview:

- The three FSMC interrupt lines are ORed in order to be connected to the NVIC
- No read FIFO
- Code execution from external memory
- No boot capability
- The targeted frequency is HCLK/2, so external access is at 12 MHz when HCLK is at 24 MHz

2.2.6 LCD parallel interface

The FSMC can be configured to interface seamlessly with most graphic LCD controllers. It supports the Intel 8080 and Motorola 6800 modes, and is flexible enough to adapt to

Table 4. High-density STM32F100xx pin definitions (continued)

Pins			Pin name	Type[1]	I/O Level[2]	Main function[3] (after reset)	Alternate functions[4]	
LQFP144	LQFP100	LQFP64					Default	Remap
120	-	-	V_{SS_10}	S	-	V_{SS_10}	-	-
121	-	-	V_{DD_10}	S	-	V_{DD_10}	-	-
122	87	-	PD6	I/O	FT	PD6	FSMC_NWAIT	USART2_RX
123	88	-	PD7	I/O	FT	PD7	FSMC_NE1	USART2_CK
124	-	-	PG9	I/O	FT	PG9	FSMC_NE2	-
125	-	-	PG10	I/O	FT	PG10	FSMC_NE3	-
126	-	-	PG11	I/O	FT	PG11	-	-
127	-	-	PG12	I/O	FT	PG12	FSMC_NE4	-
128	-	-	PG13	I/O	FT	PG13	FSMC_A24	-
129	-	-	PG14	I/O	FT	PG14	FSMC_A25	-
130	-	-	V_{SS_11}	S	-	V_{SS_11}	-	-
131	-	-	V_{DD_11}	S	-	V_{DD_11}	-	-
132	-	-	PG15	I/O	FT	PG15	-	-
133	89	55	PB3/	I/O	FT	JTDO	SPI3_SCK	PB3/TRACESWO TIM2_CH2 / SPI1_SCK
134	90	56	PB4	I/O	FT	NJTRST	SPI3_MISO	TIM3_CH1 SPI1_MISO
135	91	57	PB5	I/O	-	PB5	I2C1_SMBA/ SPI3_MOSI TIM16_BKIN	TIM3_CH2 / SPI1_MOSI
136	92	58	PB6	I/O	FT	PB6	I2C1_SCL[8]/ TIM4_CH1[8] / TIM16_CH1N	USART1_TX
137	93	59	PB7	I/O	FT	PB7	I2C1_SDA[8] / FSMC_NADV / TIM4_CH2[8] / TIM17_CH1N	USART1_RX
138	94	60	BOOT0	I	-	BOOT0	-	-
139	95	61	PB8	I/O	FT	PB8	TIM4_CH3[8]/TIM16_CH1 / HDMI_CEC	I2C1_SCL
140	96	62	PB9	I/O	FT	PB9	TIM4_CH4[8]/ TIM17_CH1	I2C1_SDA
141	97	-	PE0	I/O	FT	PE0	TIM4_ETR / FSMC_NBL0	-
142	98	-	PE1	I/O	FT	PE1	FSMC_NBL1	-
143	99	63	V_{SS_3}	S	-	V_{SS_3}	-	-
144	100	64	V_{DD_3}	S	-	V_{DD_3}	-	-

1. I = input, O = output, S = supply.
2. FT = 5 V tolerant.

Table 9. General operating conditions (continued)

Symbol	Parameter	Conditions	Min	Max	Unit
P_D	Power dissipation at T_A = 85 °C for suffix 6 or T_A = 105 °C for suffix 7(2)	LQFP144	-	666	mW
		LQFP100	-	434	
		LQFP64	-	444	
T_A	Ambient temperature for 6 suffix version	Maximum power dissipation	–40	85	°C
		Low power dissipation(3)	–40	105	
	Ambient temperature for 7 suffix version	Maximum power dissipation	–40	105	°C
		Low power dissipation(3)	–40	125	
T_J	Junction temperature range	6 suffix version	–40	105	°C
		7 suffix version	–40	125	

1. When the ADC is used, refer to *Table 51: ADC characteristics*.
2. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed $T_J$max (see *Section 6.5: Thermal characteristics on page 100*).
3. In low power dissipation state, T_A can be extended to this range as long as T_J does not exceed $T_J$max (see *Section 6.5: Thermal characteristics on page 100*).

Note: It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and operation

5.3.2 Operating conditions at power-up / power-down

Subject to general operating conditions for T_A.

Table 10. Operating conditions at power-up / power-down

Symbol	Parameter	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	0	∞	µs/V
	V_{DD} fall time rate	20	∞	

Table 16. Typical and maximum current consumptions in Stop and Standby modes

Symbol	Parameter	Conditions	Typ(1)			Max		Unit
			V_{DD}/V_{BAT} = 2.0 V	V_{DD}/V_{BAT} = 2.4 V	V_{DD}/V_{BAT} = 3.3 V	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in Stop mode	Regulator in Run mode, Low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	-	-	31	320	670	µA
		Regulator in Low-Power mode, Low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	-	-	24	305	650	
	Supply current in Standby mode	Low-speed internal RC oscillator and independent watchdog ON	-	-	3.2	-	-	
		Low-speed internal RC oscillator ON, independent watchdog OFF	-	-	3.1	-	-	
		Low-speed internal RC oscillator and independent watchdog OFF, low-speed oscillator and RTC OFF	-	-	2.2	3.9	5.7	
I_{DD_VBAT}	Backup domain supply current	Low-speed oscillator and RTC ON	1.0	1.2	1.4	2	2.3	

1. Typical values are measured at T_A = 25 °C.

Typical current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled except if it is explicitly mentioned
- When the peripherals are enabled $f_{PCLK1} = f_{HCLK}/4$, $f_{PCLK2} = f_{HCLK}/2$, $f_{ADCCLK} = f_{PCLK2}/4$

The parameters given in *Table 17* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 9*.

is the series combination of C_{L1} and C_{L2}.
Load capacitance C_L has the following formula: $C_L = C_{L1} \times C_{L2} / (C_{L1} + C_{L2}) + C_{stray}$ where C_{stray} is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.
For further details, refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website www.st.com.

Caution: To avoid exceeding the maximum value of C_{L1} and C_{L2} (15 pF) it is strongly recommended to use a resonator with a load capacitance $C_L \leq 7$ pF. Never use a resonator with a load capacitance of 12.5 pF.
Example: if you choose a resonator with a load capacitance of C_L = 6 pF, and C_{stray} = 2 pF, then $C_{L1} = C_{L2}$ = 8 pF.

Table 23. LSE oscillator characteristics (f_{LSE} = 32.768 kHz)(1)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R_F	Feedback resistor	-		-	5	-	MΩ
C_{L1} C_{L2}(2)	Recommended load capacitance versus equivalent serial resistance of the crystal (R_S)(3)	R_S = 30 KΩ		-	-	15	pF
I_2	LSE driving current	V_{DD} = 3.3 V $V_{IN} = V_{SS}$		-	-	1.4	µA
g_m	Oscillator transconductance	-		5	-	-	µA/V
$t_{SU(LSE)}$(4)	Startup time	V_{DD} is stabilized	T_A = 50 °C	-	1.5	-	s
			T_A = 25 °C	-	2.5	-	
			T_A = 10 °C	-	4	-	
			T_A = 0 °C	-	6	-	
			T_A = -10 °C	-	10	-	
			T_A = -20 °C	-	17	-	
			T_A = -30 °C	-	32	-	
			T_A = -40 °C	-	60	-	

1. Based on characterization, not tested in production.
2. Refer to the note and caution paragraphs above the table.
3. The oscillator selection can be optimized in terms of supply current using an high quality resonator with small R_S value for example MSIV-TIN32.768 kHz. Refer to crystal manufacturer for more details
4. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer

Figure 18. Asynchronous multiplexed PSRAM/NOR write waveforms

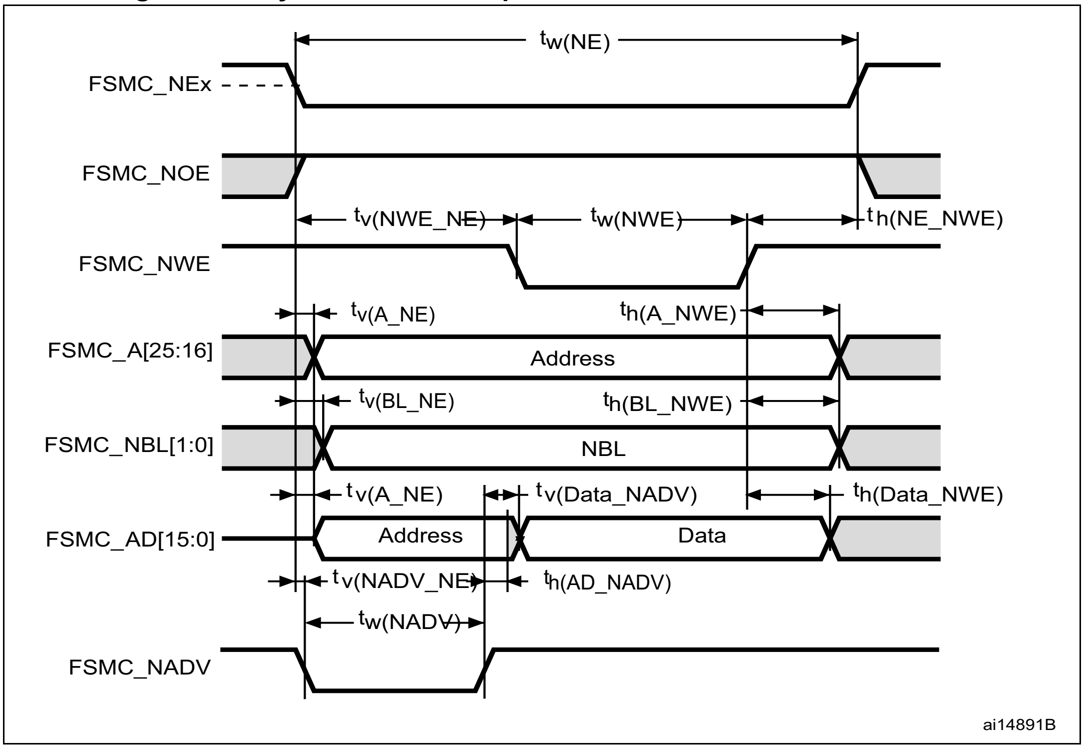


Table 33. Asynchronous multiplexed PSRAM/NOR write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FSMC_NE low time	$5T_{HCLK} - 1$	$5T_{HCLK} + 2$	ns
$t_{v(NWE\_NE)}$	FSMC_NEx low to FSMC_NWE low	$2T_{HCLK}$	$2T_{HCLK} + 1$	ns
$t_{w(NWE)}$	FSMC_NWE low time	$2T_{HCLK} - 1$	$2T_{HCLK} + 2$	ns
$t_{h(NE\_NWE)}$	FSMC_NWE high to FSMC_NE high hold time	$T_{HCLK} - 1$	-	ns
$t_{v(A\_NE)}$	FSMC_NEx low to FSMC_A valid	-	7	ns
$t_{v(NADV\_NE)}$	FSMC_NEx low to FSMC_NADV low	3	5	ns
$t_{w(NADV)}$	FSMC_NADV low time	$T_{HCLK} - 1$	$T_{HCLK} + 1$	ns
$t_{h(AD\_NADV)}$	FSMC_AD (address) valid hold time after FSMC_NADV high	$T_{HCLK} - 3$	-	ns
$t_{h(A\_NWE)}$	Address hold time after FSMC_NWE high	$4T_{HCLK}$	-	ns
$t_{v(BL\_NE)}$	FSMC_NEx low to FSMC_BL valid	-	1.6	ns
$t_{h(BL\_NWE)}$	FSMC_BL hold time after FSMC_NWE high	$T_{HCLK} - 1.5$	-	ns
$t_{v(Data\_NADV)}$	FSMC_NADV high to Data valid	-	$T_{HCLK} + 1.5$	ns
$t_{h(Data\_NWE)}$	Data hold time after FSMC_NWE high	$T_{HCLK} - 5$	-	ns

1. C_L = 15 pF.
2. Preliminary values.

Synchronous waveforms and timings

Figure 19 through *Figure 22* represent synchronous waveforms and *Table 35* through *Table 37* provide the corresponding timings. The results shown in these tables are obtained with the following FSMC configuration:

- BurstAccessMode = FSMC_BurstAccessMode_Enable;
- MemoryType = FSMC_MemoryType_CRAM;
- WriteBurst = FSMC_WriteBurst_Enable;
- CLKDivision = 1; (0 is not supported, see the STM32F10xxx reference manual)
- DataLatency = 1 for NOR Flash; DataLatency = 0 for PSRAM

Figure 19. Synchronous multiplexed NOR/PSRAM read timings

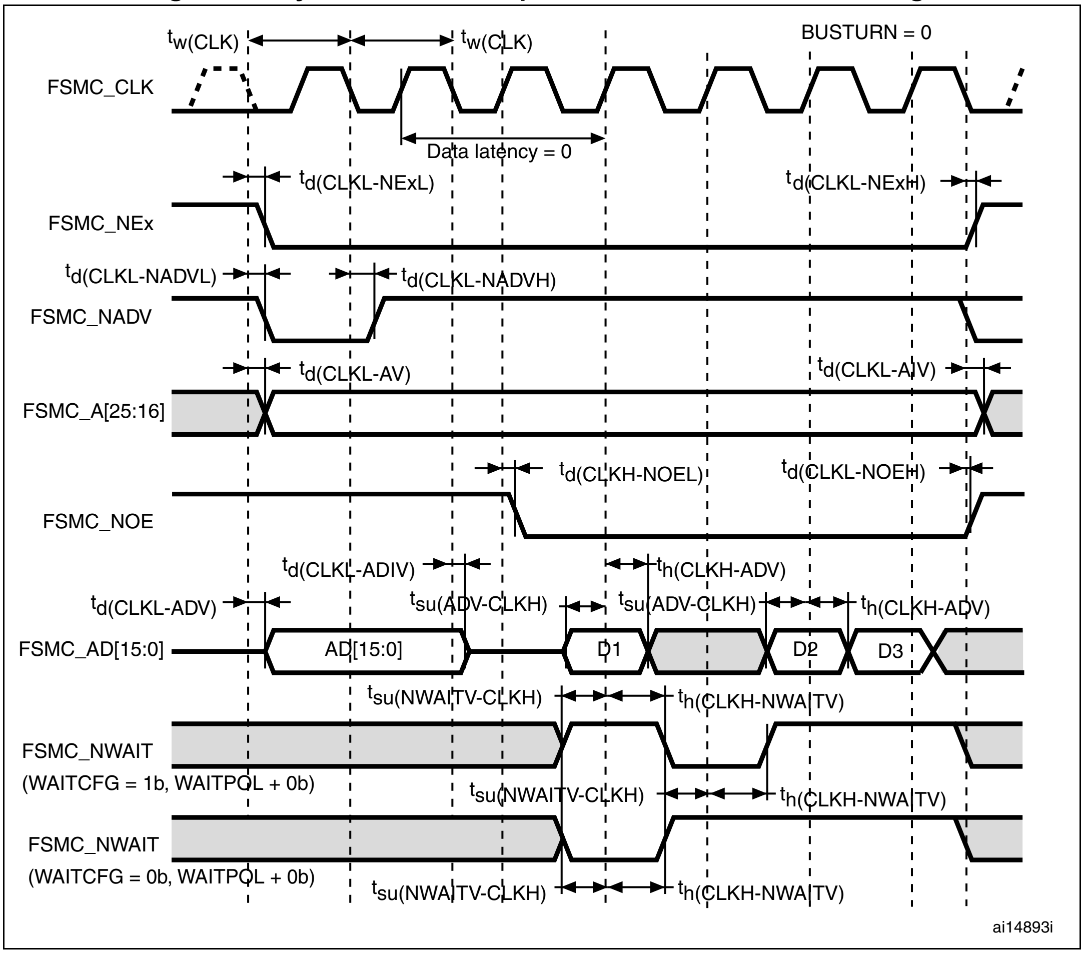
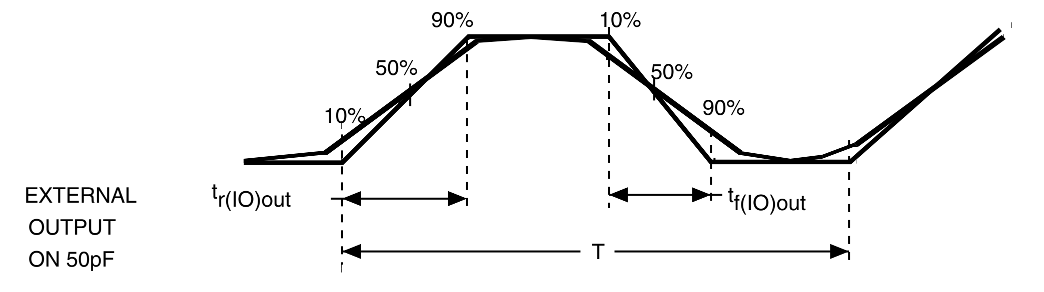


Figure 27. I/O AC characteristics definition



5.3.15 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see *Table 43*).

Unless otherwise specified, the parameters given in *Table 46* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 9*.

Table 46. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}$(1)	NRST Input low level voltage	-	–0.5	-	0.8	V
$V_{IH(NRST)}$(1)	NRST Input high level voltage	-	2	-	V_{DD}+0.5	V
$V_{hys(NRST)}$	NRST Schmitt trigger voltage hysteresis	-	-	200	-	mV
R_{PU}	Weak pull-up equivalent resistor(2)	$V_{IN} = V_{SS}$	30	40	50	kΩ
$V_{F(NRST)}$(1)	NRST Input filtered pulse	-	-	-	100	ns
$V_{NF(NRST)}$(1)	NRST Input not filtered pulse	-	300	-	-	ns

1. Guaranteed by design, not tested in production.
2. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).

5.3.16 TIMx characteristics

The parameters given in *Table 47* are guaranteed by design.

Refer to *Section 5.3.13: I/O current injection characteristics* for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 47. TIMx characteristics

Symbol	Parameter	Conditions(1)	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time	-	1	-	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 24 MHz	41.7	-	ns
f_{EXT}	Timer external clock frequency on CHx(2)		0	$f_{TIMxCLK}/2$	MHz
		$f_{TIMxCLK}$ = 24 MHz	0	12	MHz
Res_{TIM}	Timer resolution	-	-	16	bit
$t_{COUNTER}$	16-bit counter clock period when the internal clock is selected	-	1	65536	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 24 MHz	-	2730	µs
t_{MAX_COUNT}	Maximum possible count	-	-	65536 × 65536	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 24 MHz	-	178	s

1. TIMx is used as a general term to refer to the TIM1, TIM2, TIM3, TIM4, TIM5, TIM15, TIM16 and TIM17 timers.
2. CHx is used as a general term to refer to CH1 to CH4 for TIM1, TIM2, TIM3, TIM4 and TIM5, to the CH1 to CH2 for TIM15, and to CH1 for TIM16 and TIM17.

5.3.17 Communications interfaces

I^2C interface characteristics

Unless otherwise specified, the parameters given in *Table 48* are preliminary values derived from tests performed under the ambient temperature, f_{PCLK1} frequency and V_{DD} supply voltage conditions summarized in *Table 9*.

The STM32F100xx value line I^2C interface meets the requirements of the standard I^2C communication protocol with the following restrictions: the I/O pins SDA and SCL are mapped to are not “true” open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present.

The I^2C characteristics are described in *Table 48*. Refer also to *Section 5.3.13: I/O current injection characteristics* for more details on the input/output alternate function characteristics (SDA and SCL).

SPI interface characteristics

Unless otherwise specified, the parameters given in *Table 50* are preliminary values derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 9*.

Refer to *Section 5.3.13: I/O current injection characteristics* for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 50. SPI characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	12	MHz
		Slave mode	-	12	
$t_{r(SCK)}$ $t_{f(SCK)}$	SPI clock rise and fall time	Capacitive load: C = 30 pF		8	ns
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	30	70	%
$t_{su(NSS)}$(1)	NSS setup time	Slave mode	$4t_{PCLK}$	-	ns
$t_{h(NSS)}$(1)	NSS hold time	Slave mode	$2t_{PCLK}$	-	
$t_{w(SCKH)}$(1) $t_{w(SCKL)}$(1)	SCK high and low time	Master mode, f_{PCLK} = 24 MHz, presc = 4	50	60	
$t_{su(MI)}$(1) $t_{su(SI)}$(1)	Data input setup time	Master mode	5	-	
		Slave mode	5	-	
$t_{h(MI)}$(1)	Data input hold time	Master mode	5	-	
$t_{h(SI)}$(1)		Slave mode	4	-	
$t_{a(SO)}$(1)(2)	Data output access time	Slave mode, f_{PCLK} = 24 MHz	0	$3t_{PCLK}$	
$t_{dis(SO)}$(1)(3)	Data output disable time	Slave mode	2	10	
$t_{v(SO)}$(1)	Data output valid time	Slave mode (after enable edge)	-	25	
$t_{v(MO)}$(1)	Data output valid time	Master mode (after enable edge)	-	5	
$t_{h(SO)}$(1)	Data output hold time	Slave mode (after enable edge)	15	-	
$t_{h(MO)}$(1)		Master mode (after enable edge)	2	-	

1. Preliminary values.
2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z

Table 52. R_{AIN} max for f_{ADC} = 12 MHz[1]

T_s (cycles)	t_S (µs)	R_{AIN} max (kΩ)
1.5	0.125	0.4
7.5	0.625	5.9
13.5	1.125	11.4
28.5	2.375	25.2
41.5	3.45	37.2
55.5	4.625	50
71.5	5.96	NA
239.5	20	NA

1. Guaranteed by design, not tested in production.

Table 53. ADC accuracy - limited test conditions[1][2]

Symbol	Parameter	Test conditions	Typ	Max	Unit
ET	Total unadjusted error	f_{PCLK2} = 24 MHz, f_{ADC} = 12 MHz, R_{AIN} < 10 kΩ, V_{DDA} = 3 V to 3.6 V V_{REF+} = V_{DDA} T_A = 25 °C Measurements made after ADC calibration	±1.5	±2.5	LSB
EO	Offset error		±1	±2	
EG	Gain error		±0.5	±1.5	
ED	Differential linearity error		±1.5	±2	
EL	Integral linearity error		±1.5	±2	

1. ADC DC accuracy values are measured after internal calibration.
2. Preliminary values.

Table 54. ADC accuracy[1] [2] [3]

Symbol	Parameter	Test conditions	Typ	Max	Unit
ET	Total unadjusted error	f_{PCLK2} = 24 MHz, f_{ADC} = 12 MHz, R_{AIN} < 10 kΩ, V_{DDA} = 2.4 V to 3.6 V T_A = Full operating range Measurements made after ADC calibration	±2	±5	LSB
EO	Offset error		±1.5	±2.5	
EG	Gain error		±1.5	±3	
ED	Differential linearity error		±1.5	±2.5	
EL	Integral linearity error		±1.5	±4.5	

1. ADC DC accuracy values are measured after internal calibration.
2. Better performance could be achieved in restricted V_{DD}, frequency, V_{REF} and temperature ranges.
3. Preliminary values.

Note: ADC accuracy vs. negative injection current: Injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

5.3.20 Temperature sensor characteristics

Table 56. TS characteristics

Symbol	Parameter	Min	Typ	Max	Unit
T_L(1)	V_{SENSE} linearity with temperature	-	±1	±2	°C
Avg_Slope(1)	Average slope	4.0	4.3	4.6	mV/°C
V_{25}(1)	Voltage at 25°C	1.32	1.41	1.50	V
t_{START}(2)	Startup time	4	-	10	µs
T_{S_temp}(3)(2)	ADC sampling time when reading the temperature	-	-	17.1	µs

1. Guaranteed by characterization, not tested in production.
2. Guaranteed by design, not tested in production.
3. Shortest sampling time can be determined in the application by multiple iterations.

Table 57. LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat package mechanical data

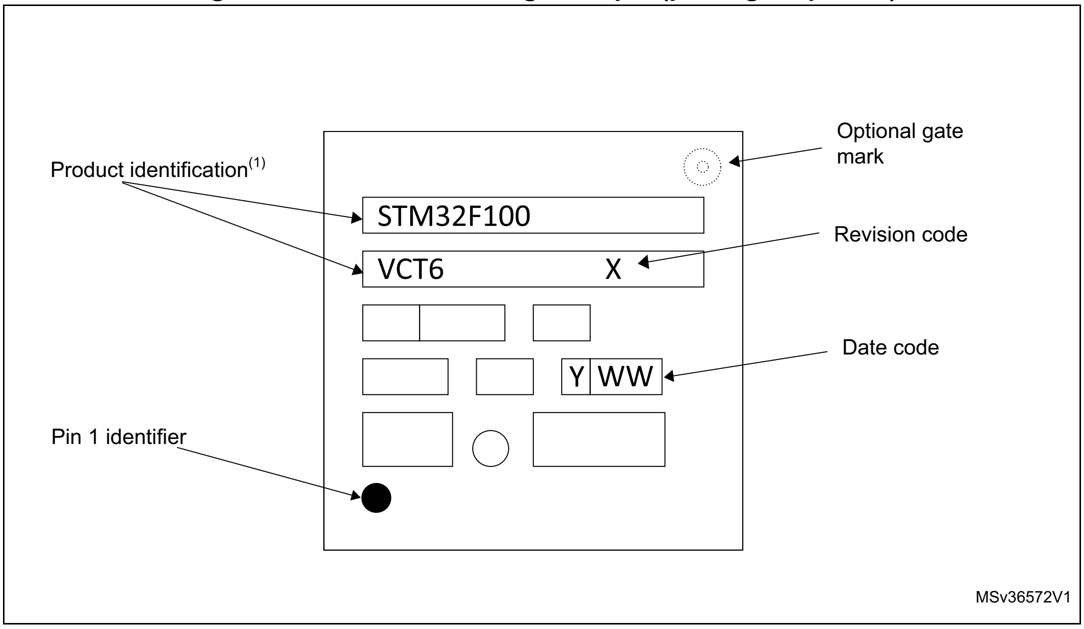
Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	21.800	22.000	22.200	0.8583	0.8661	0.8740
D1	19.800	20.000	20.200	0.7795	0.7874	0.7953
D3	-	17.500	-	-	0.6890	-
E	21.800	22.000	22.200	0.8583	0.8661	0.8740
E1	19.800	20.000	20.200	0.7795	0.7874	0.7953
E3	-	17.500	-	-	0.6890	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Device marking for LQFP100

The following figure shows the device marking for the LQFP100 package.

Figure 43.LQFP100 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

6.5 Thermal characteristics

The maximum chip junction temperature ($T_J$max) must never exceed the values given in *Table 9: General operating conditions on page 38*.

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

T_J max = T_A max + (P_D max x Θ_{JA})

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

$P_{I/O}$ max represents the maximum power dissipation on output pins where:

$$P_{I/O} \max = \Sigma (V_{OL} \times I_{OL}) + \Sigma((V_{DD} - V_{OH}) \times I_{OH}),$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 60. Package thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	**Thermal resistance junction-ambient** LQFP 144 - 20 × 20 mm / 0.5 mm pitch	35	°C/W
	Thermal resistance junction-ambient LQFP 100 - 14 × 14 mm / 0.5 mm pitch	40	
	Thermal resistance junction-ambient LQFP 64 - 10 × 10 mm / 0.5 mm pitch	49	

6.5.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.

6.5.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the ordering information scheme shown in *Table 61: Ordering information scheme*.

Each temperature range suffix corresponds to a specific guaranteed ambient temperature at maximum dissipation and, to a specific maximum junction temperature.

As applications do not commonly use the STM32F100xx at maximum dissipation, it is useful to calculate the exact power consumption and junction temperature to determine which temperature range will be best suited to the application.

The following examples show how to calculate the temperature range needed for a given application.

Example: high-performance application

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 82 °C (measured according to JESD51-2), I_{DDmax} = 50 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V and maximum 8 I/Os used at the same time in output mode at low level with I_{OL} = 20 mA, V_{OL}= 1.3 V

$P_{INTmax} =$ 50 mA × 3.5 V= 175 mW

$P_{IOmax} = 20$ × 8 mA × 0.4 V + 8 × 20 mA × 1.3 V = 272 mW

This gives: P_{INTmax} = 175 mW and P_{IOmax} = 272 mW

$P_{Dmax} =$ 175 + 272 = 447 mW

Thus: P_{Dmax} = 447 mW

Using the values obtained in *Table 60* T_{Jmax} is calculated as follows:

– For LQFP64, 49 °C/W

T_{Jmax} = 82 °C + (49 °C/W × 447 mW) = 82 °C + 20.1 °C = 102.1 °C

This is within the range of the suffix 6 version parts (–40 < T_J < 105 °C).

In this case, parts must be ordered at least with the temperature range suffix 6 (see *Table 61: Ordering information scheme*).

Example 2: High-temperature application

Using the same rules, it is possible to address applications that run at high ambient temperatures with a low dissipation, as long as junction temperature T_J remains within the specified range.

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 115 °C (measured according to JESD51-2), I_{DDmax} = 20 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V

$P_{INTmax} =$ 20 mA × 3.5 V= 70 mW

$P_{IOmax} = 20$ × 8 mA × 0.4 V = 64 mW

This gives: P_{INTmax} = 70 mW and P_{IOmax} = 64 mW:

$P_{Dmax} =$ 70 + 64 = 134 mW

Thus: P_{Dmax} = 134 mW